



Scaling Interconnect Densities

Meeting the Growing Demand for Chiplet Integration

Robin Davis – Director of Business Development

Tim Olson - CEO

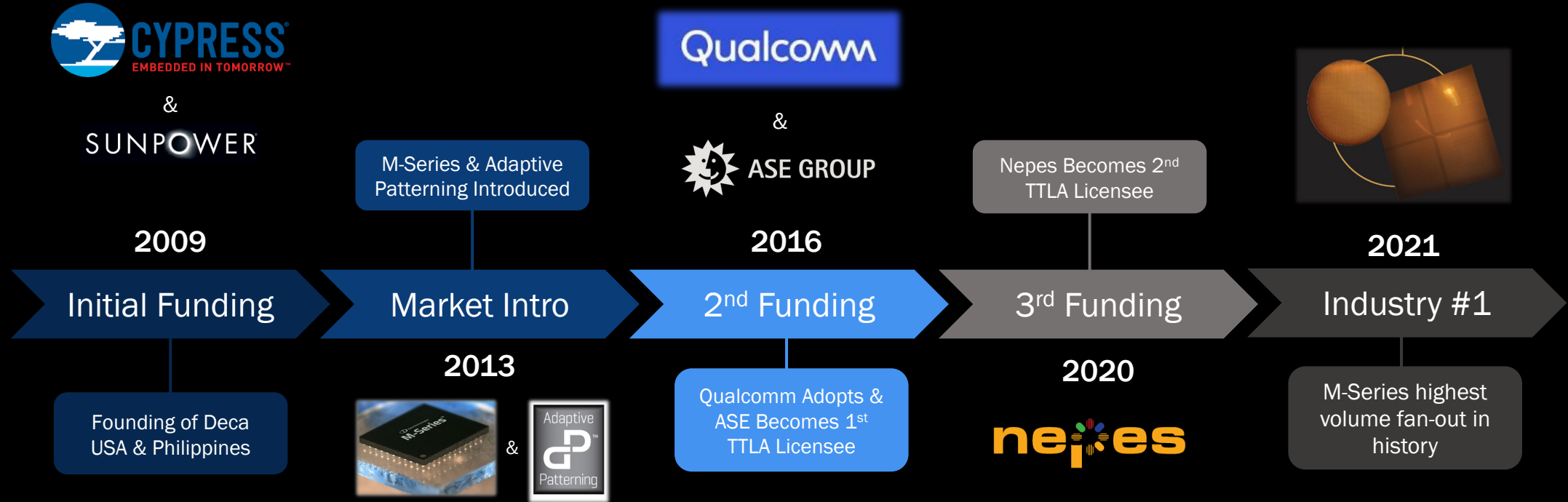


19TH INTERNATIONAL CONFERENCE & EXHIBITION ON
DEVICE PACKAGING
FOUNTAIN HILLS, AZ • WWW.DEVICEPACKAGING.ORG • MARCH 13-16, 2023

Outline

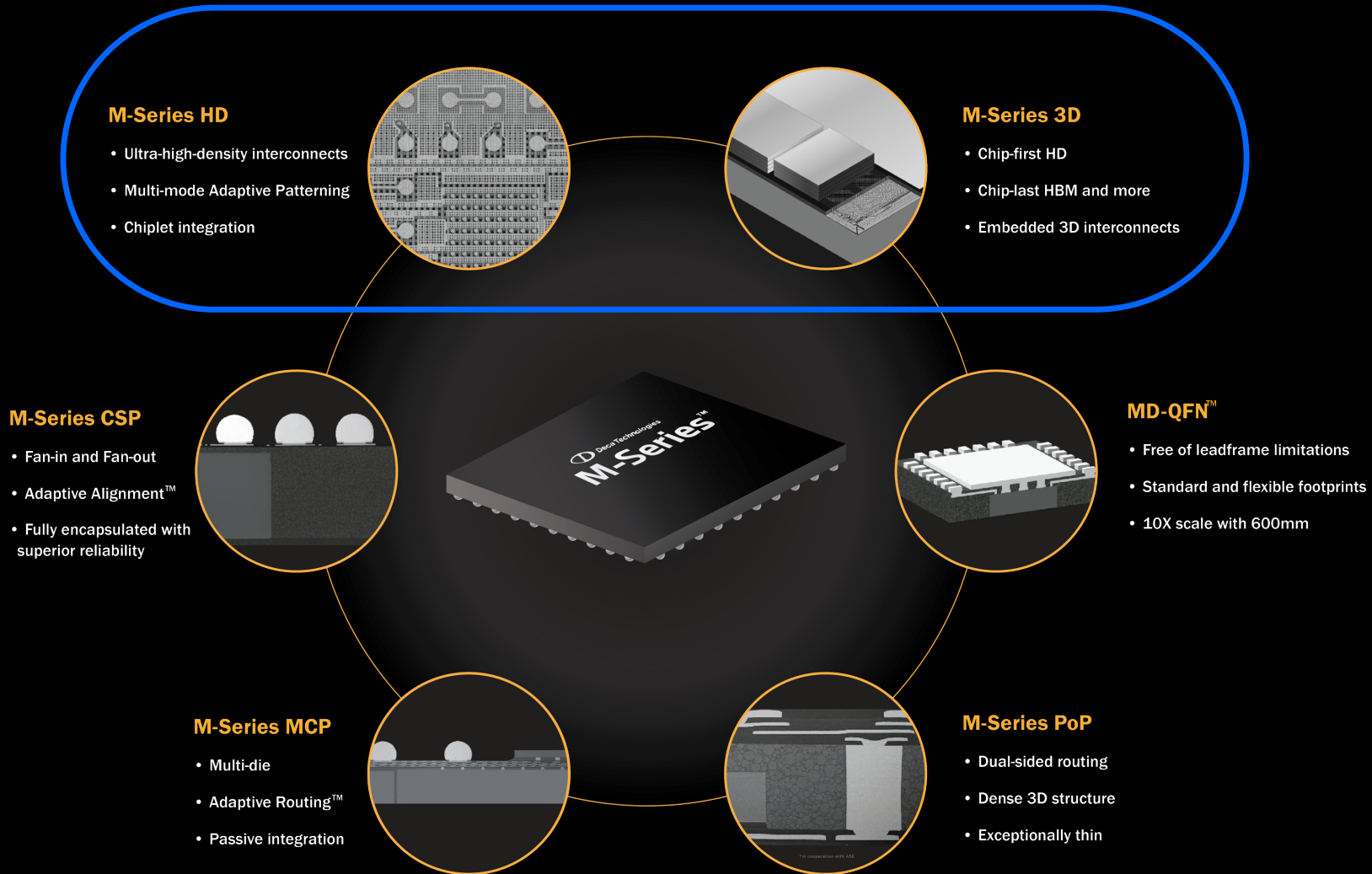
- Introduction
- Industry Perspective
- Leading Examples
- What's Next
- Conclusion

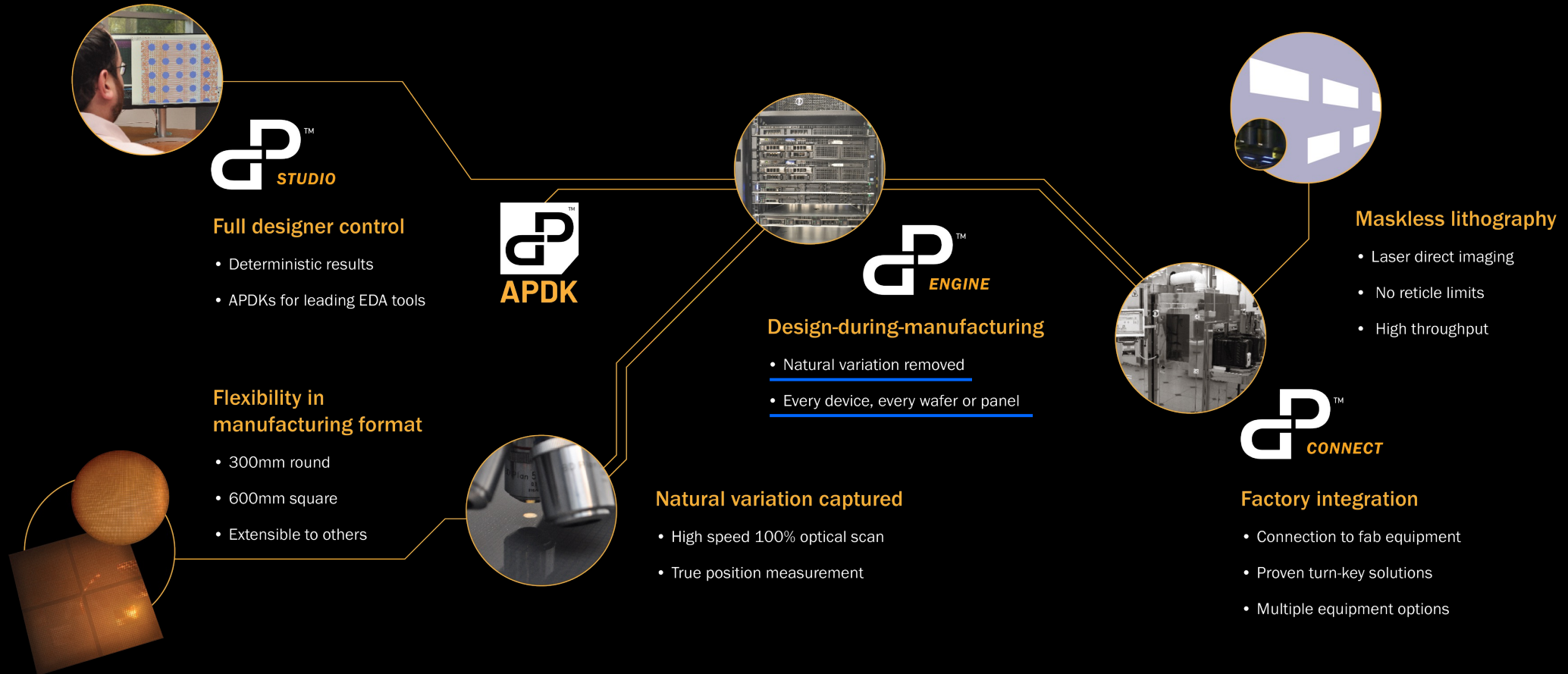
DECA Company Introduction



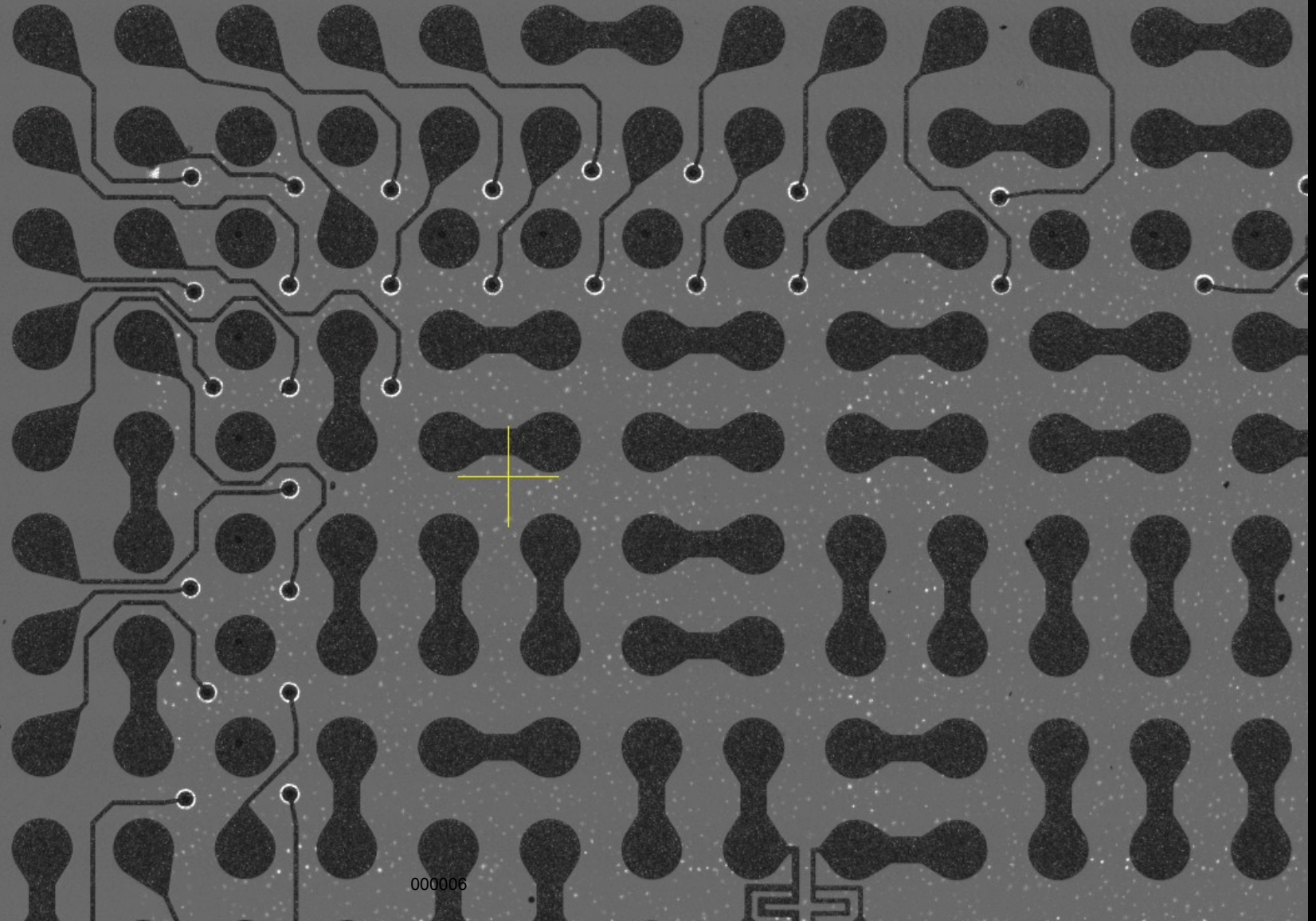
Deca is the #1 independent technology development & licensing company in the advanced packaging industry¹

¹Fan-out WLP & PLP Technologies 2021- Markets & Technology Report, Yole Developpement, June 2021





Adaptive Routing in Action

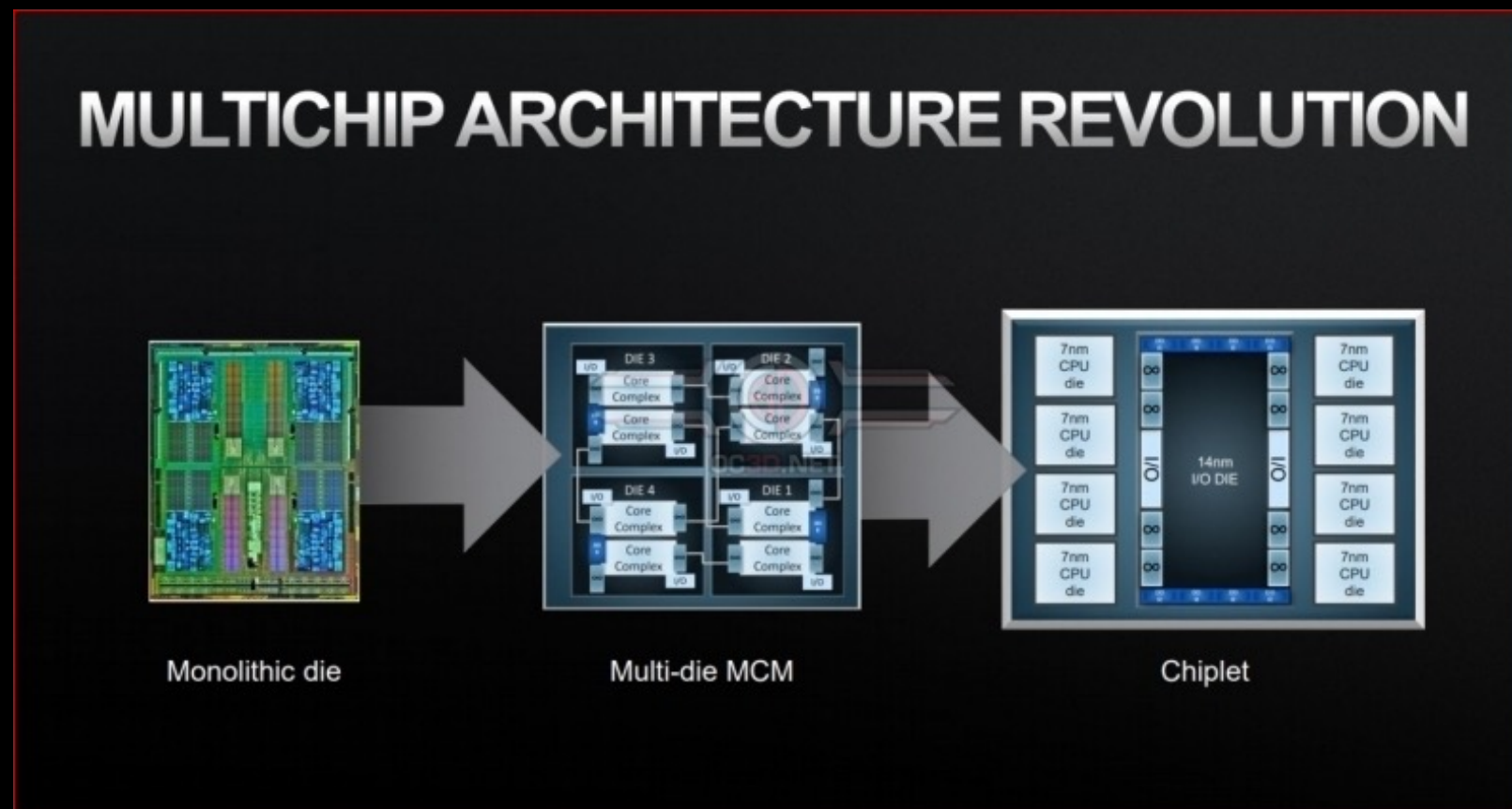


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Industry Perspective

Industry leading semiconductor companies are moving on from the monolithic IC invented 60 years



AMD

intel

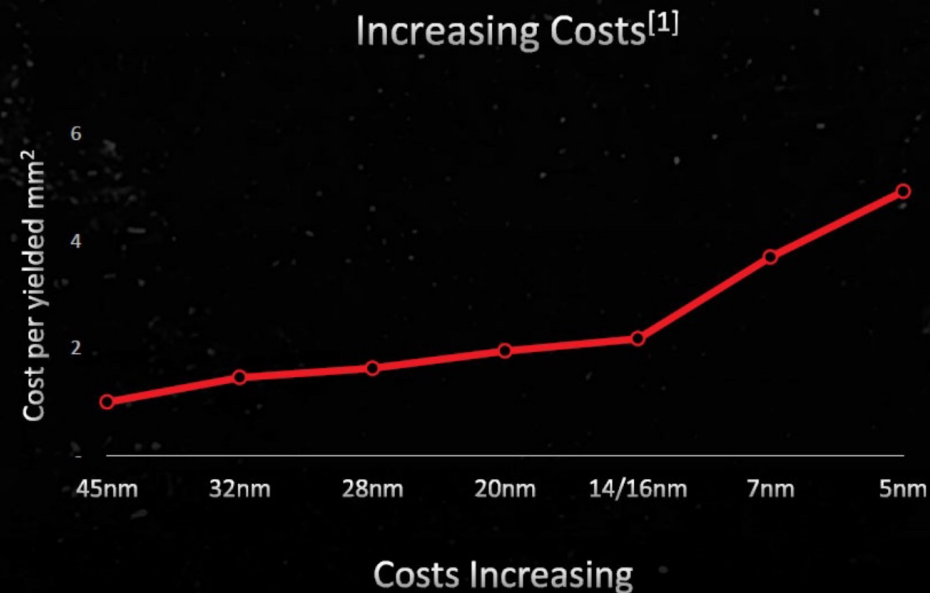
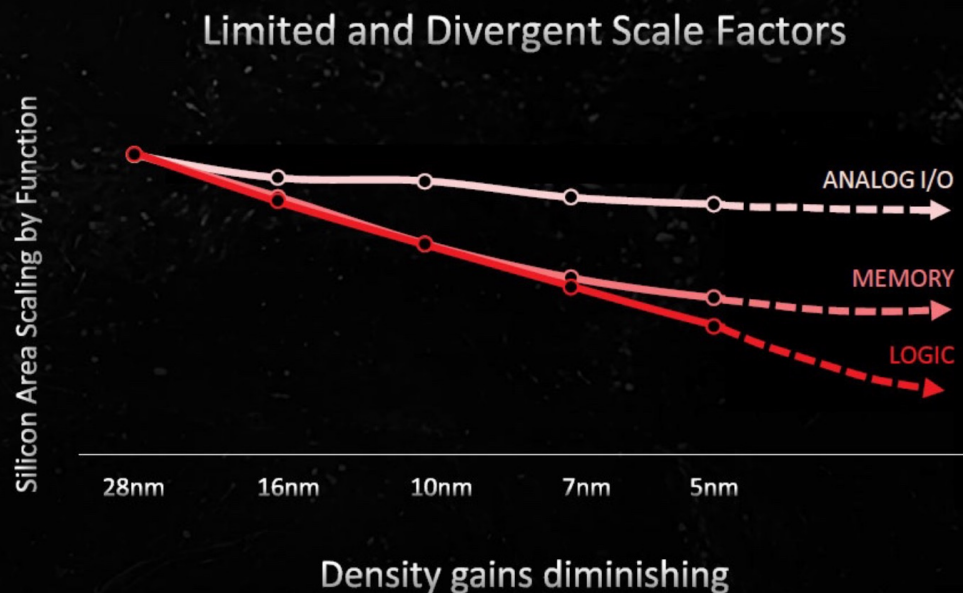
Qualcomm

&

Many more

... to chiplets & heterogeneous integration

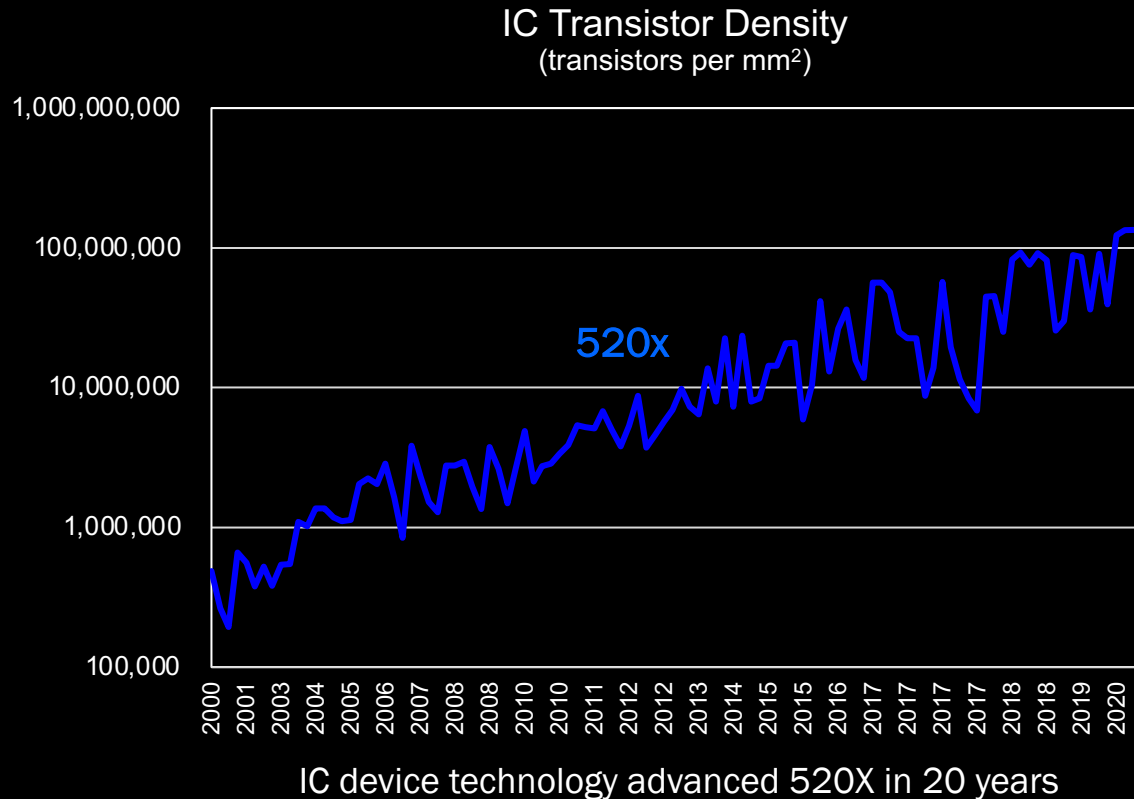
CHIPLET TECHNOLOGY OUR MOTIVATION



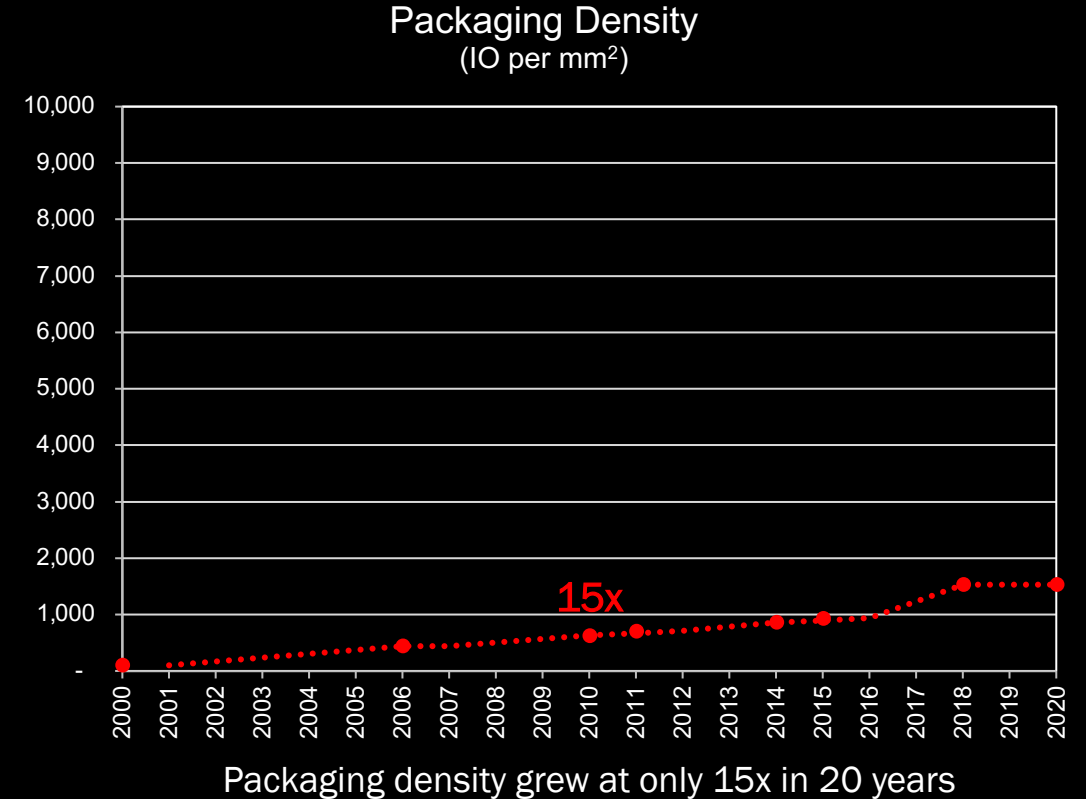
Moore's Law Slowing – Packaging Far Behind

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Semiconductor ICs > 500X density increase in past 20 years vs. 15X for packaging



Source: Multiple industry sources compiled at en.wikipedia.org/wiki/Transistor_Count



Sources: 1. Chip scale Review: March-April 2020, IO/mm² derived from die pad pitch data
2. Tech Search Intl, Advanced Packaging Update, Vol 2, 2020

Packaging interface density lagging ICs by orders of magnitude

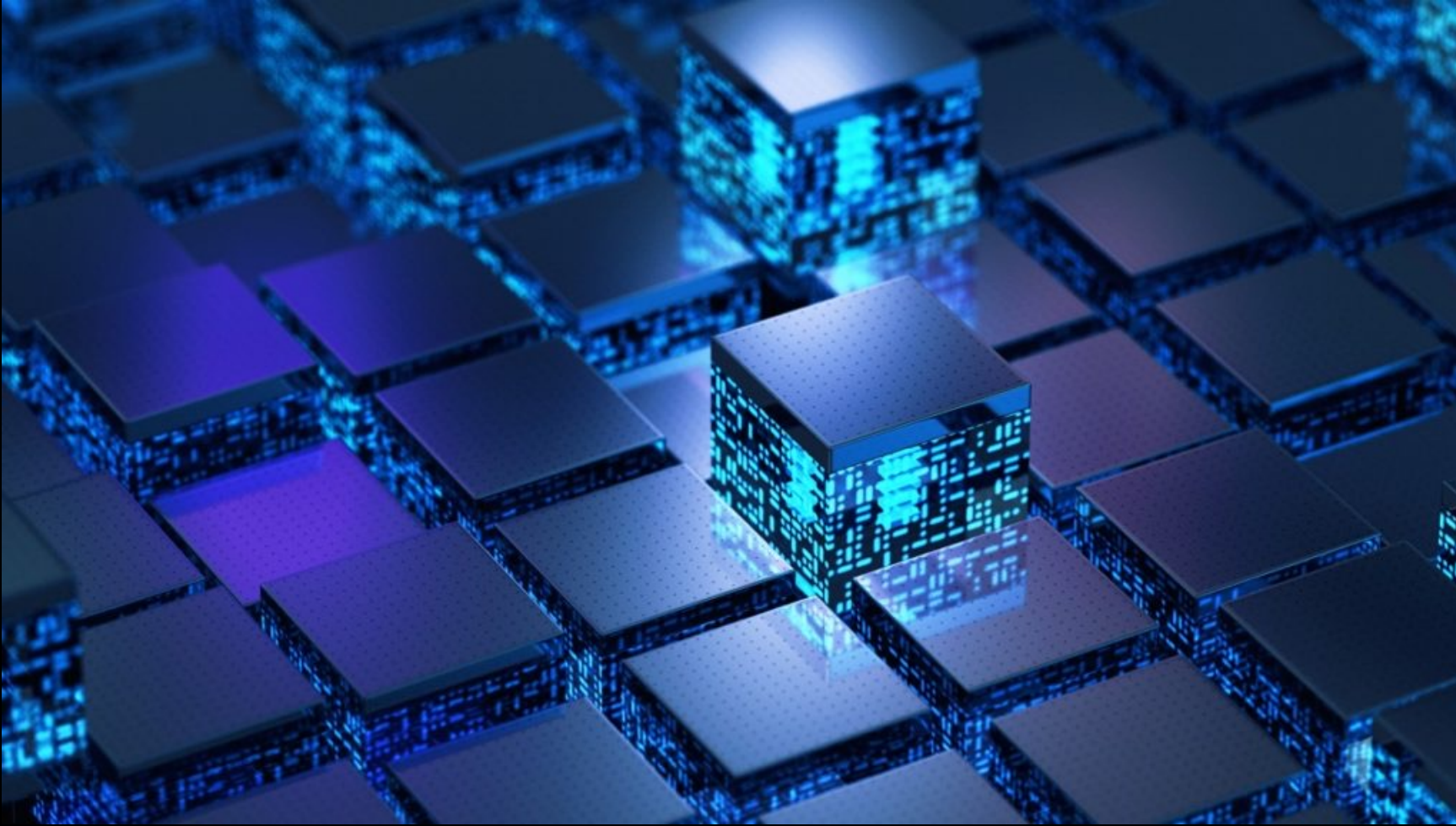


However, some recent breakthroughs have occurred!

Industry Perspective

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How will the industry connect all the chiplets?



Outline

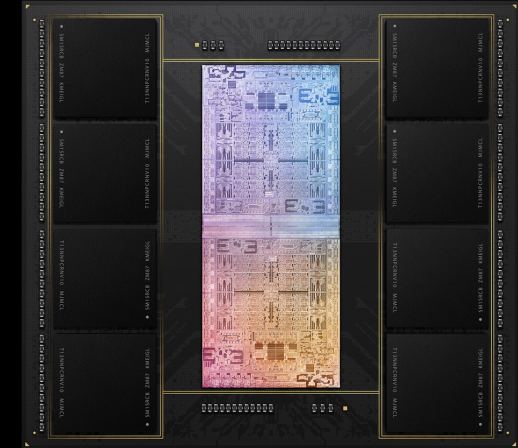
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Apple Mac Studio with M1 Ultra Processor – March 2022

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M1 Ultra Processor
(Created with advanced packaging)



- Two 5nm M1 Max die, 840mm² (total both die)
- 64 or 128GB DRAM (total in 8 packages)

The world's most powerful personal computer, over 22 trillion operations per second

A Look Inside the Apple M1 Ultra

1. M1 Max die-to-die spacing: $110\mu\text{m}$
2. M1 Max die A thickness: $587\mu\text{m}$
3. InFo-L ball pitch: Variable 100-150 μm

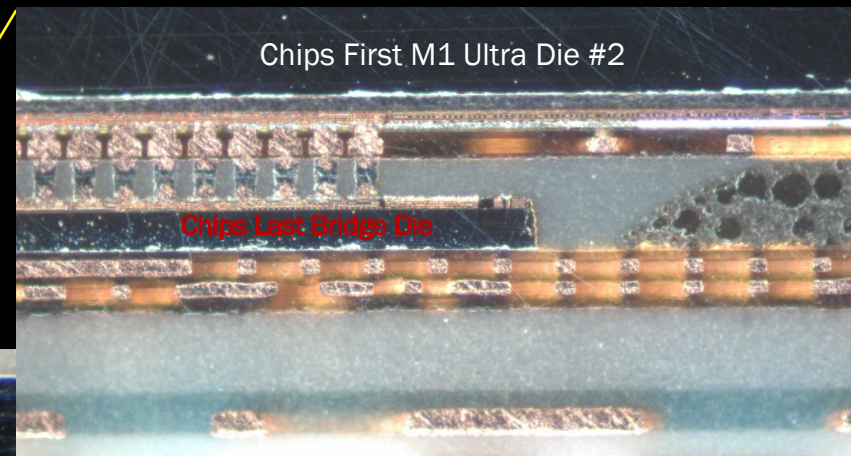
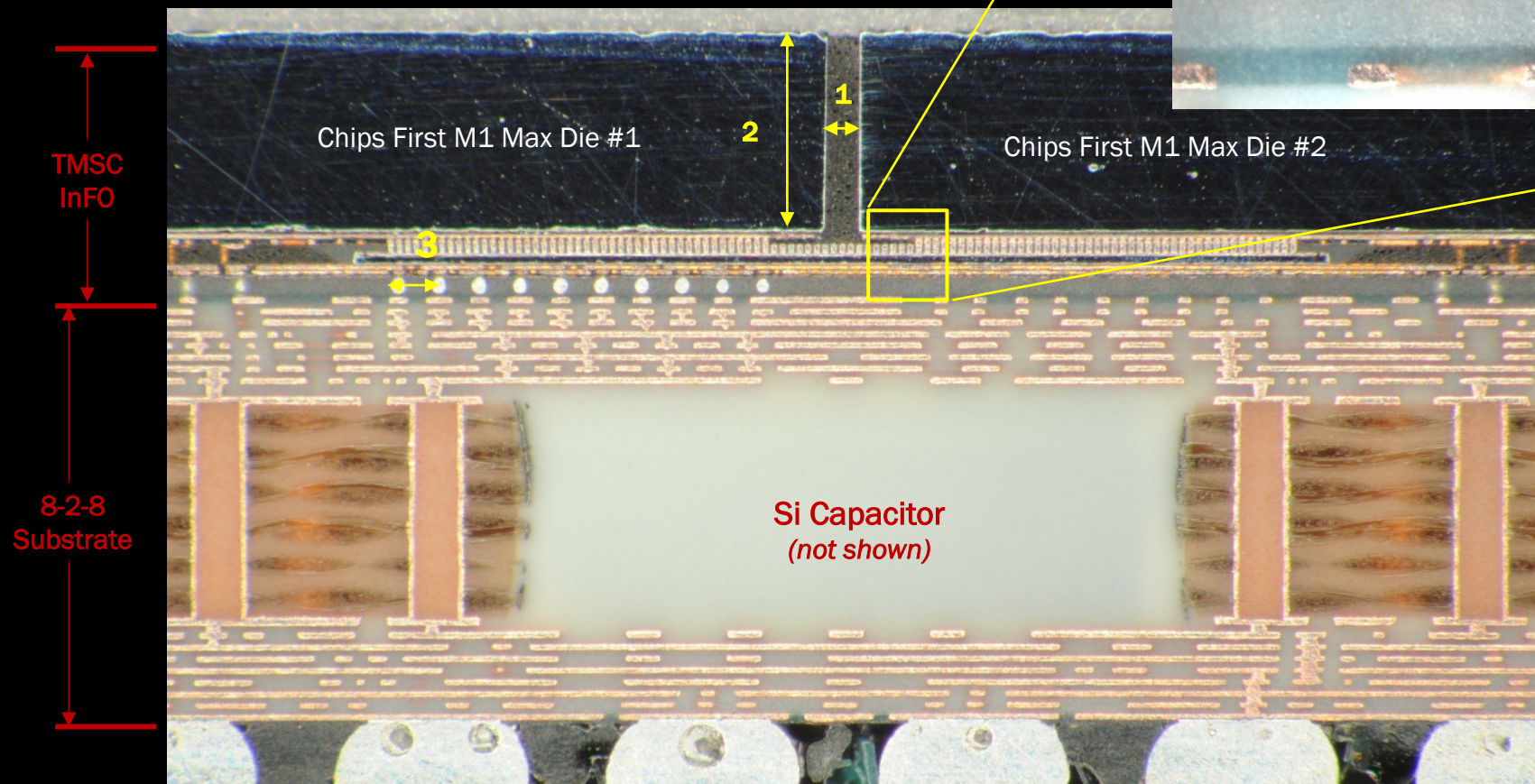


Photo source: Prismark/Binghamton University

A Look Inside the Apple M1 Ultra

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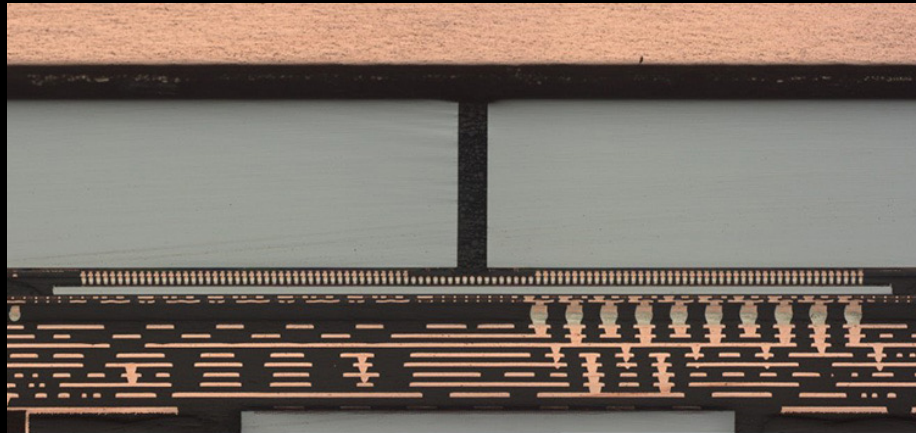
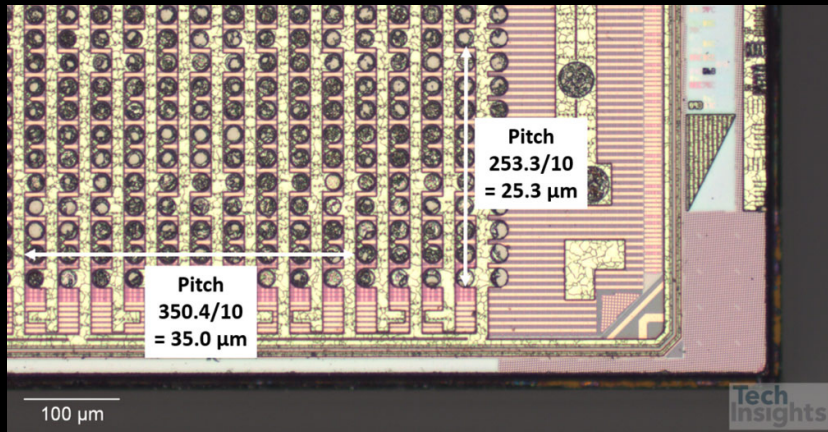


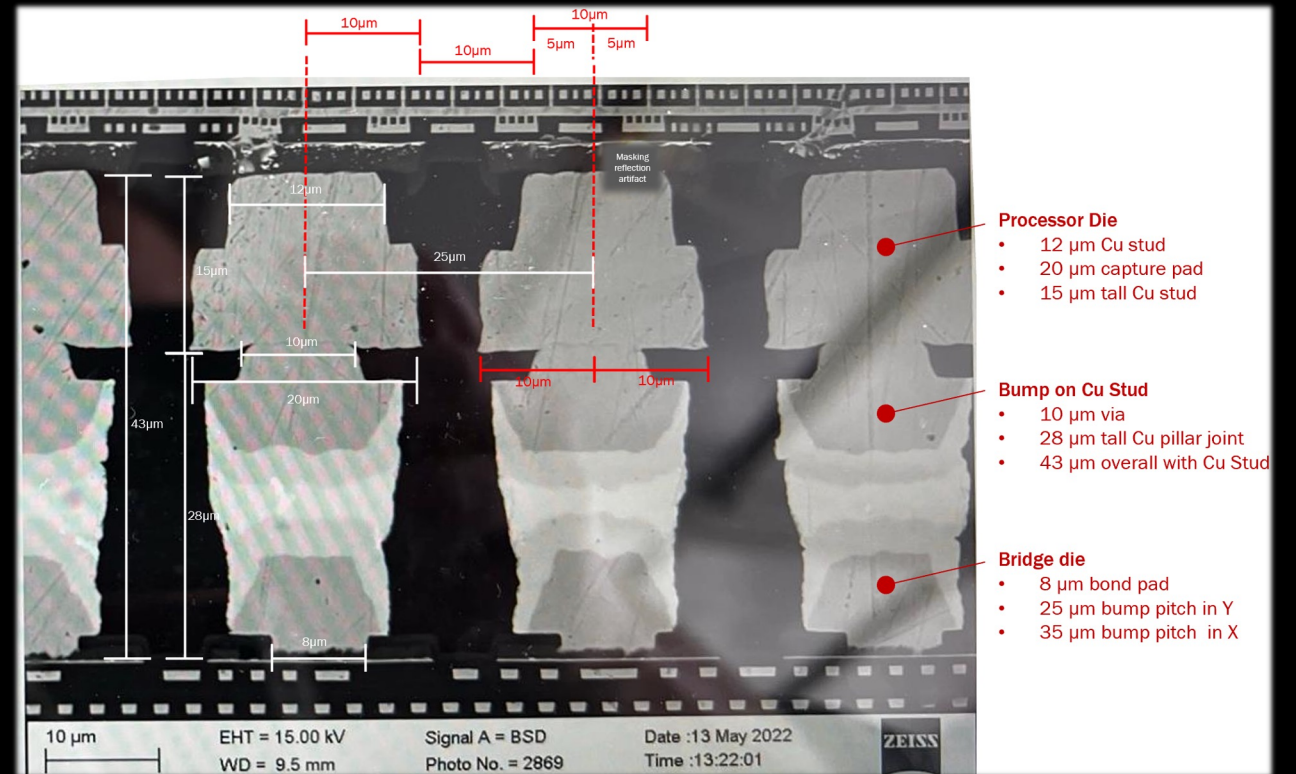
Photo source: Apple M1 Ultra SoC, Yole SystemPlus 2022



<https://www.techinsights.com/blog/apple-joins-3d-fabric-portfolio-m1-ultra>

Semiconductor Industry's Most Advanced Packaging (1st half of 2022)

- Ultra fine pitch Cu pillar flip chip bridge die (25μm x 35μm)
- 10,000 bond pads per die for bridge (leading density when introduced)
- 2.5 TB/s estimated bandwidth



Processor Die

- 12 μm Cu stud
- 20 μm capture pad
- 15 μm tall Cu stud

Bump on Cu Stud

- 10 μm via
- 28 μm tall Cu pillar joint
- 43 μm overall with Cu Stud

Bridge die

- 8 μm bond pad
- 25 μm bump pitch in Y
- 35 μm bump pitch in X

65x72mm TSMC InFO-L fan-out on substrate

- Chips up chips first M1 Max die (2 die)

Major challenge in manufacturing with < 4μm die shift required (x, y & θ after chip attach & mold)

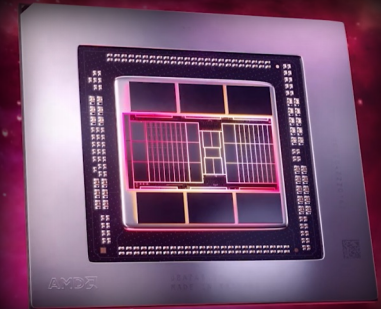
High-end Gaming PCs with AMD RDNA3 – August 2022

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AMD

RDNA3 GPU



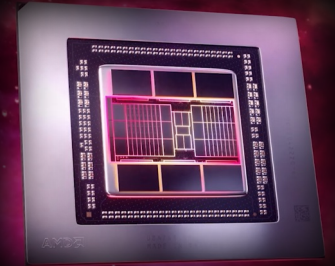
The world's most powerful gaming computers, over 28 teraflops of performance

A Look Inside AMD's RDNA3

RDNA3 GPU

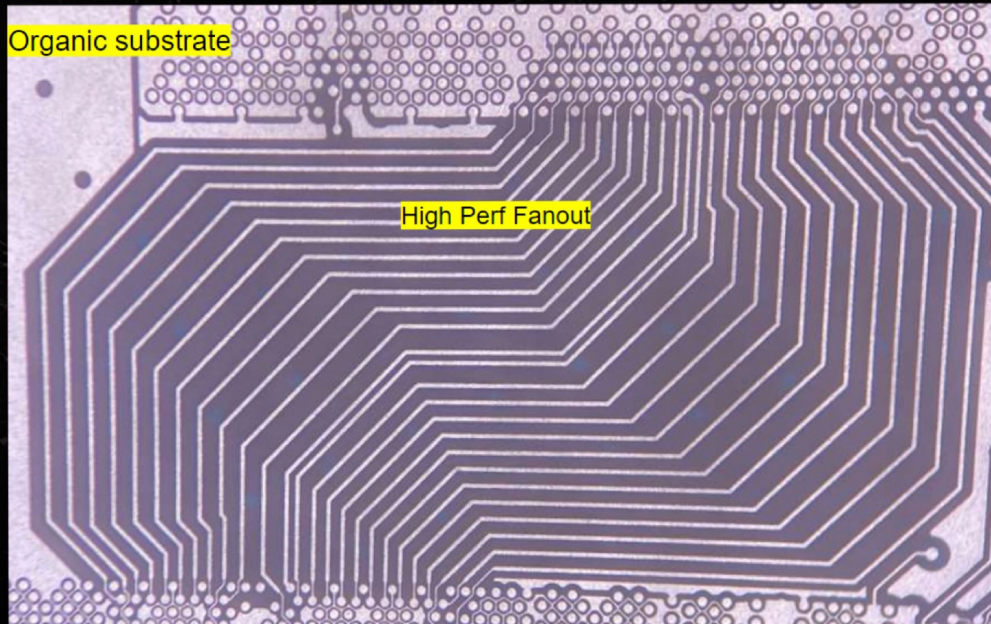
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Breakthrough density increase moving from laminate substrates to **chips first fan-out technology**



AMD

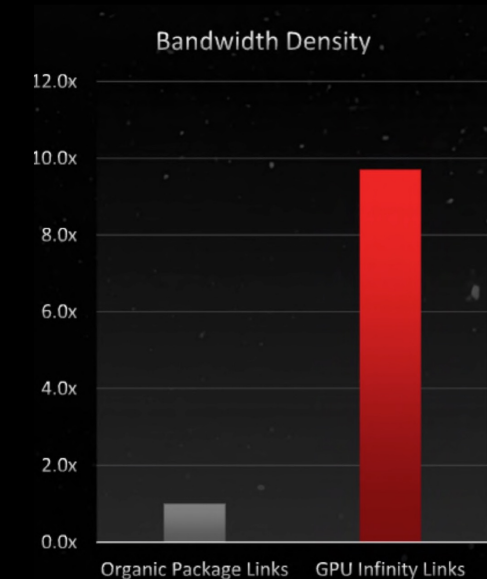
CHIPLET TECHNOLOGY HIGH PERFORMANCE FANOUT INTERCONNECT



25 wires on organic substrate
compared to 50 wires on High
Performance Fanout

Images approximately to scale

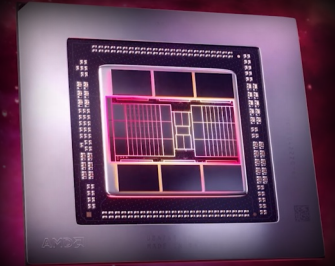
AMD
together we advance gaming



AMD
together we advance gaming

- 98% size reduction in size with advanced packaging technology (fan-out)
- Order of magnitude increase in bandwidth

A Look Inside AMD's RDNA3



The New Most Advanced Packaging (2nd half of 2022)

- Very fine pitch 35 μ m pitch die bond pads
- 4 layers of RDL – no complicated bridge die required (RDL only)
- 5.3 TB/s spec performance (double the Apple A1 of six months earlier)

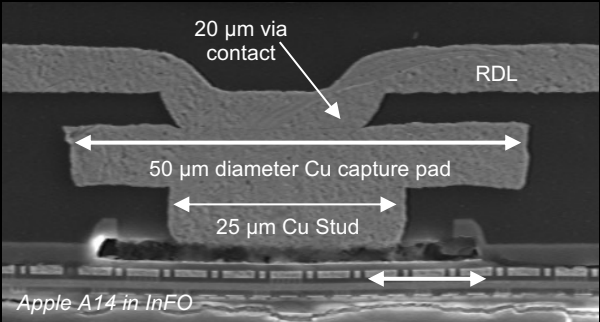


8 μ m via & 13 μ m capture pads

- Again, like the M1 ultra, < 4 μ m total die shift required (x, y, & θ after chip attach & mold)
- Significant manufacturing challenge

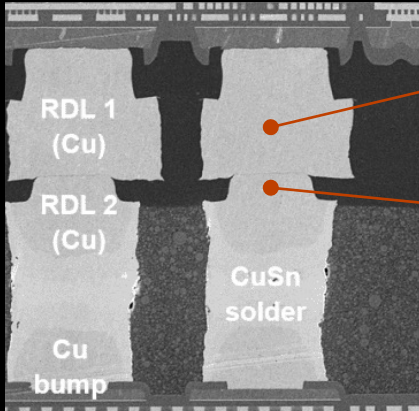
Accounting for die shift in the M1 Ultra

TSMC InFO



Source: Prismark iPhone 12 Analysis Jan'21

Apple M1 Ultra

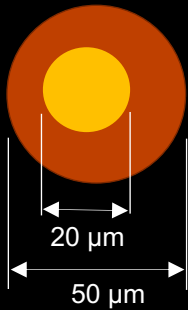
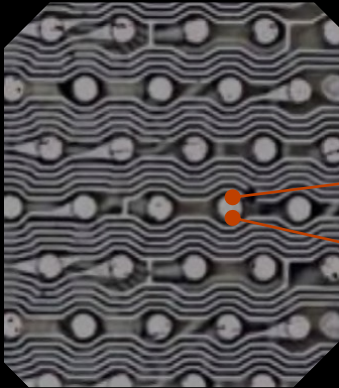


15 μ m diameter Cu capture pad

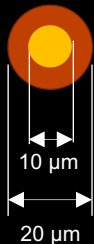
10 μ m via diameter

https://www.semiconductor-digest.com/apples-m1-ultra-does-use-info_lsi-or-is-it-cowos-l/

AMD RDNA3



Large Cu capture pad
(extra layer added to Cu stud)



Small ratio
precision die attach
low throughput



Have we reached the practical limits of fan-out scaling?

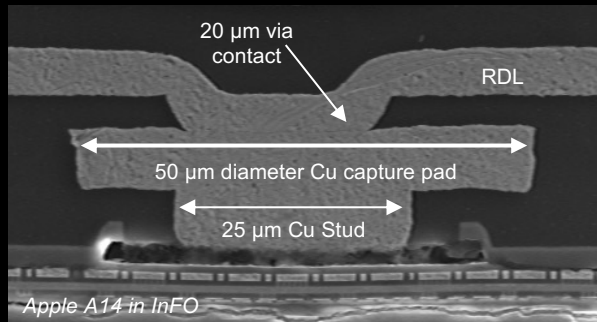
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Adaptive Patterning Eliminates the Capture Pad

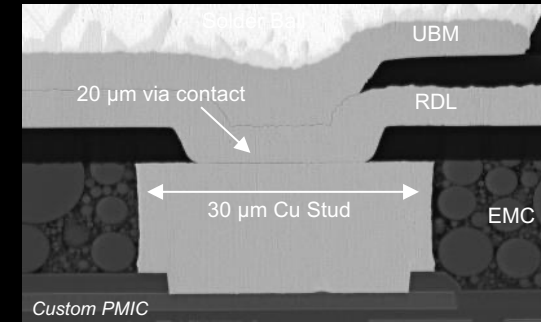
Breaking through the die bond pad interface barriers of the past

TSMC InFO



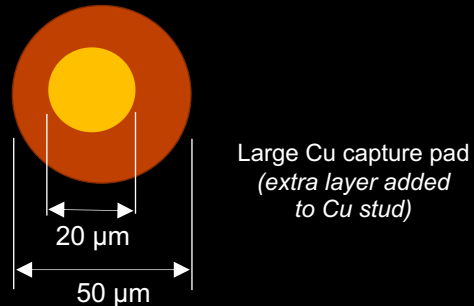
Source: Prismark iPhone 12 Analysis Jan'21

M-Series with Adaptive Patterning

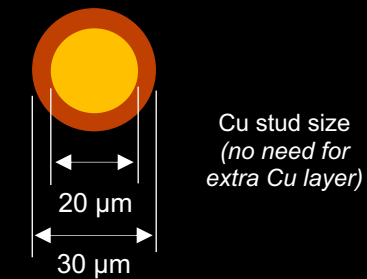


Source: Prismark iPhone 12 Analysis Jan'21

Via connection without Adaptive Patterning



Via connection with Adaptive Patterning

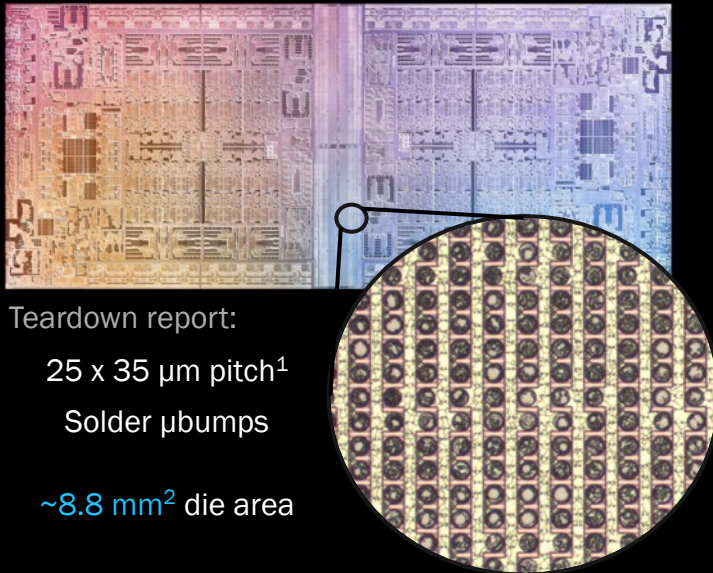


Industry Leading Die-to-Die Bandwidth (M-Series™ with Adaptive Patterning®)

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- Industry's most advanced die-to-die interconnect density as of today
- Integrates two M1 Max die
- > 10,000 die-to-die connections

Silicon Bridge



Teardown report:

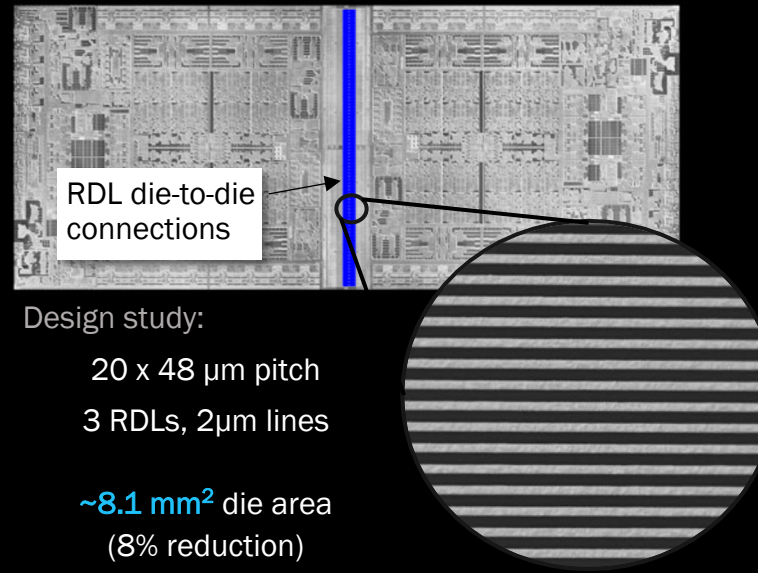
25 x 35 μm pitch¹

Solder μbumps

~8.8 mm^2 die area

¹Techsearch International Inc.

M-Series Gen 2



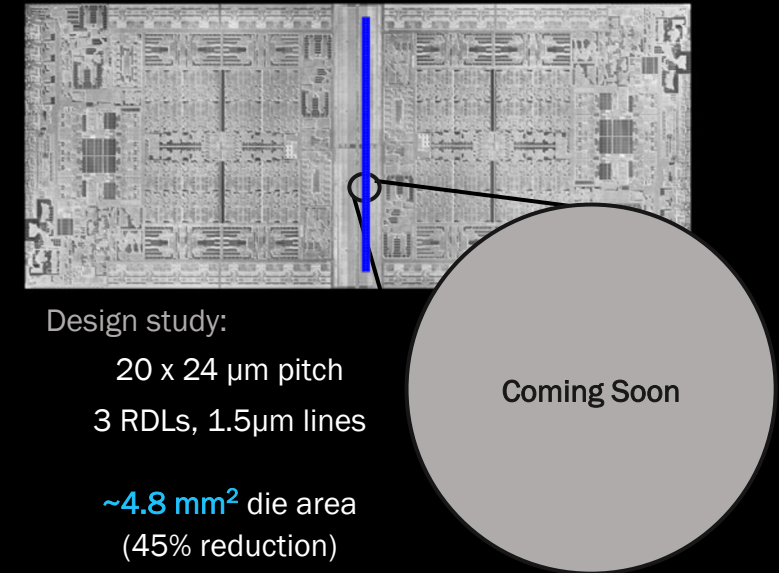
Design study:

20 x 48 μm pitch

3 RDLs, 2 μm lines

~8.1 mm^2 die area
(8% reduction)

M-Series Direct - MDx



Design study:

20 x 24 μm pitch

3 RDLs, 1.5 μm lines

~4.8 mm^2 die area
(45% reduction)

Coming Soon

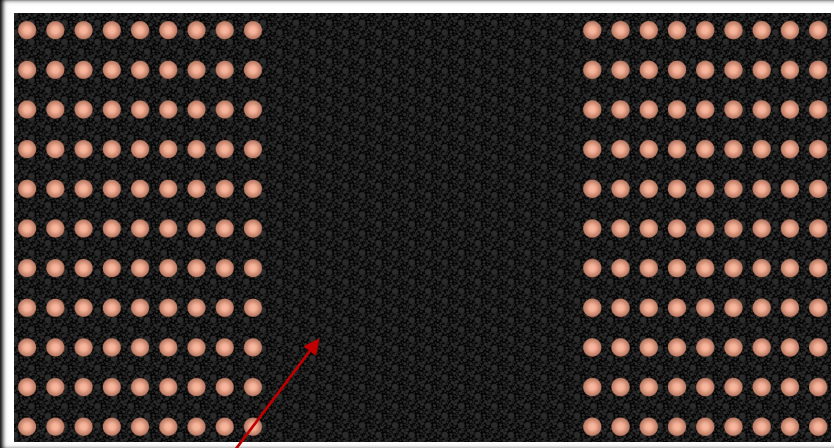
MDx removes capture pads all together

Industry Leading Die-to-Die Bandwidth (M-Series™ with Adaptive Patterning®)

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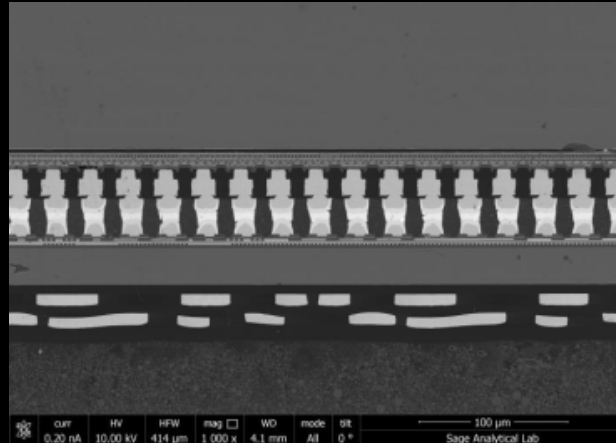
Matching TSMC's Apple M1 Ultra benchmark & significantly outperforming it

1. TSMC InFO Bridge Die Solution



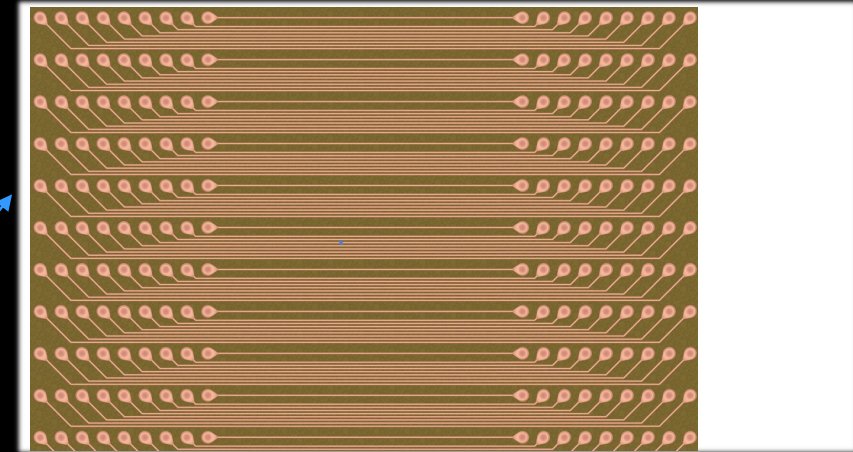
Die-to-Die requires bridge die
15.8 μm UBM pad
25 x 35 μm pitch

TSMC requires bridge die with
challenging flip chip attach



All drawings to scale

2. Deca M-Series Gen 2C (to scale)



White box =
TSMC M1 Size

Die-to-Die interconnect in RDL
1.5 μm line & space, 14 μm capture pad
20 x 40 μm pitch

Deca solutions much
simpler with RDL-only

3. Deca Gen 2 MDx (M-Series Direct with no capture pads)

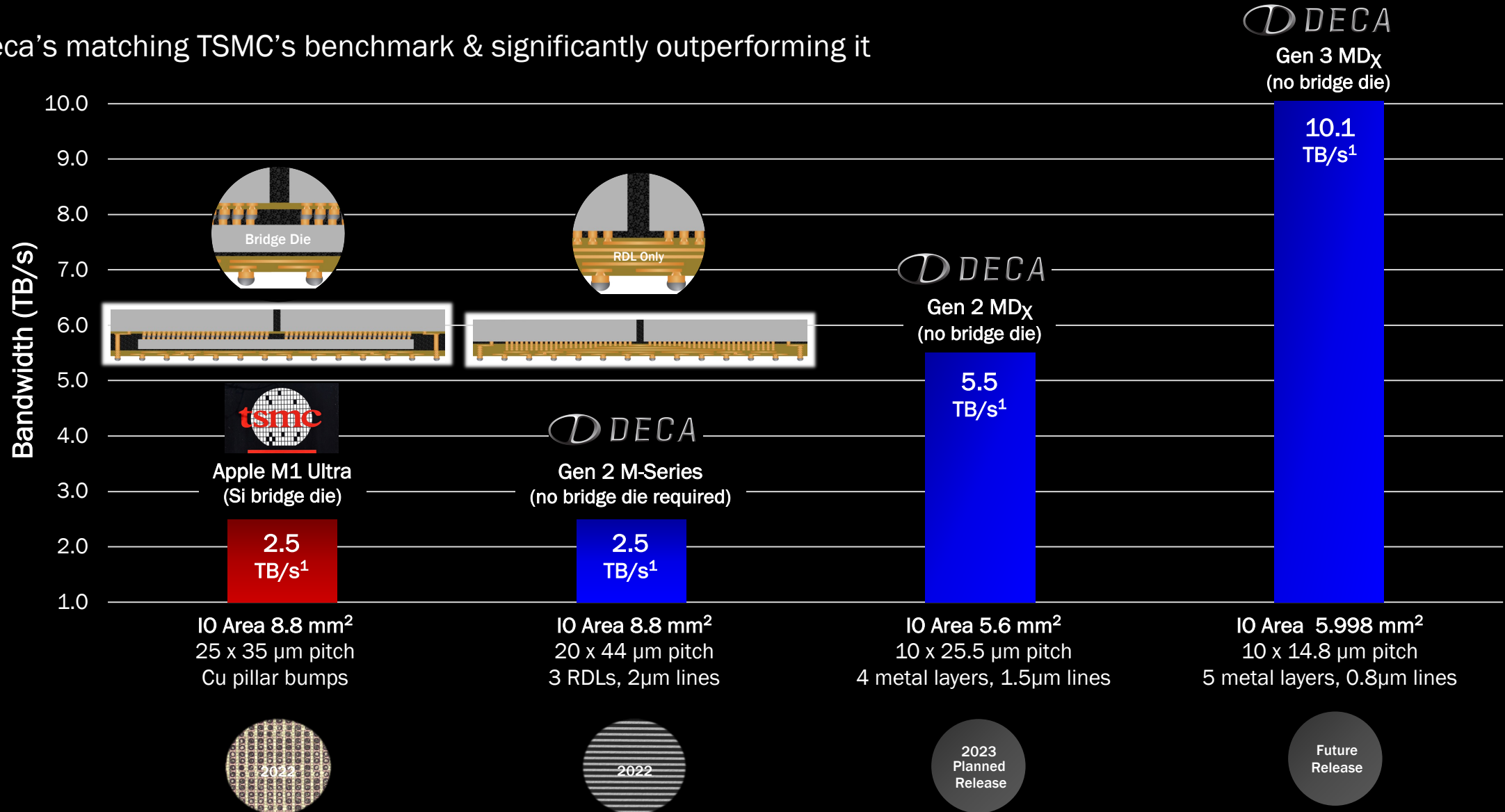


MDx interface size
(image under NDA)

Industry Leading Die-to-Die Bandwidth (M-Series™ with Adaptive Patterning®)

24

Deca's matching TSMC's benchmark & significantly outperforming it



¹ Assumes 20mm beachfront with the same per-wire bandwidth (Gbps) for all cases

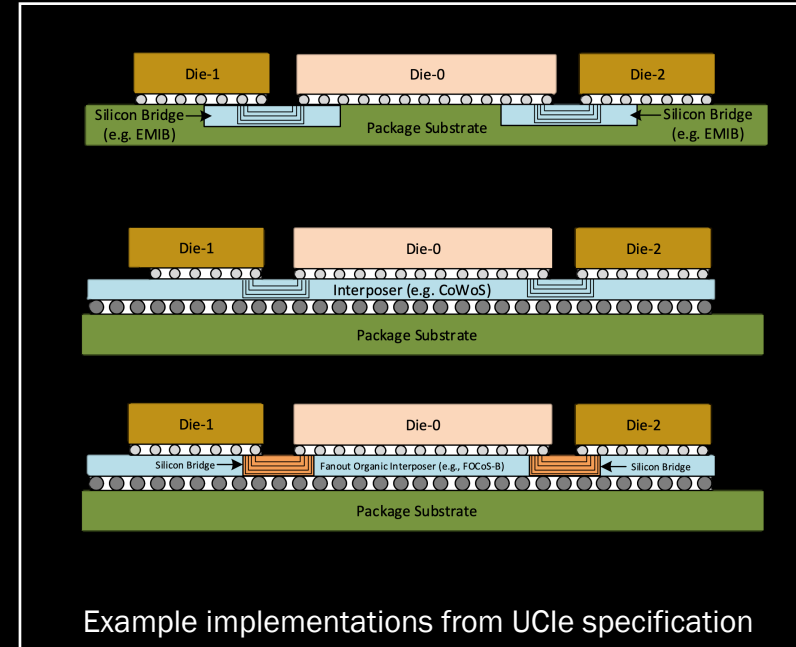
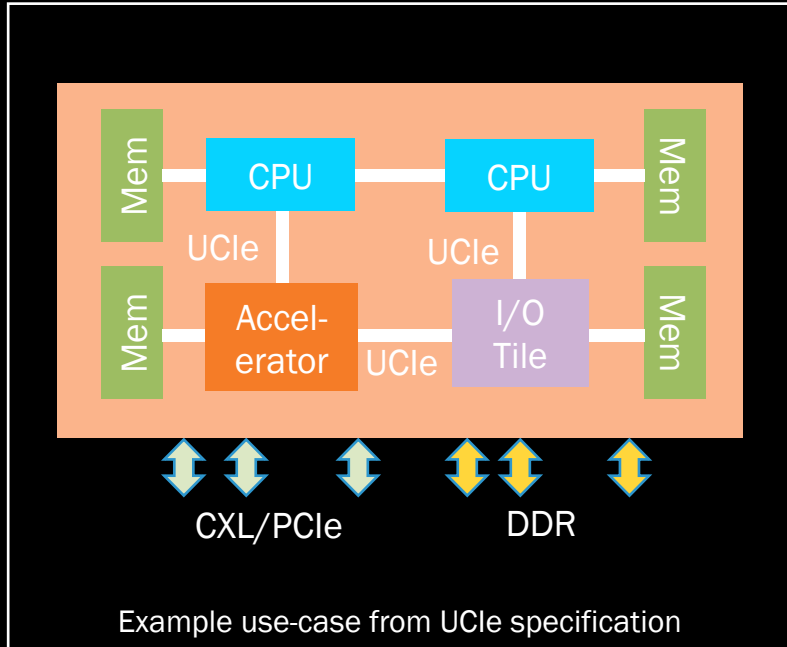
² Estimated IO area includes signal bumps for one die; ground bumps and guard traces vary depending on implementation

Note: Multiple patents issued & pending

Chiplet Standardization

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Primary goal: provide an open, multi-protocol, on-package interconnect standard for connecting multiple dies



Standard UCIe footprint originally targeting Si bridge, Si interposer, CoWoS

Major IP suppliers are now offering UCIe PHYs and controllers

Chiplet Standardization

Alphawave collaboration underway for UCle layout and electrical simulation

✓ Initial electrical extraction completed for two layout options:

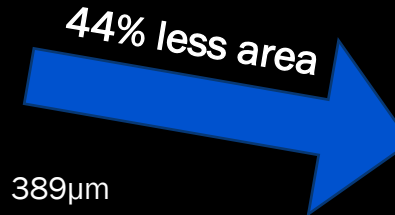
45μm Staggered Pitch

Standard Footprint

0.41mm²



1043μm



20x48μm Pitch

Area Optimized

0.23mm²



446μm

522μm

- Standard UCle footprint originally targeting Si bridge, Si interposer, CoWoS
- Layout completed with Gen 2 M-Series 5-RDL stack-up

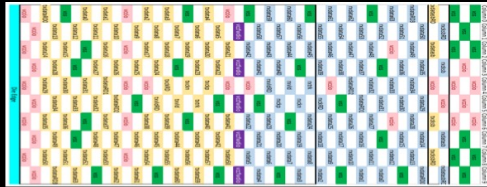
- Optimized for Gen 2 M-Series capabilities
- Layout completed with 5 RDL Gen 2 M-Series stack-up
- Simulation results show 4 RDL stack-up is feasible

Simulation results show excellent insertion loss and low crosstalk

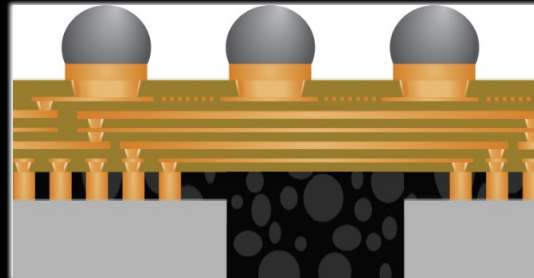
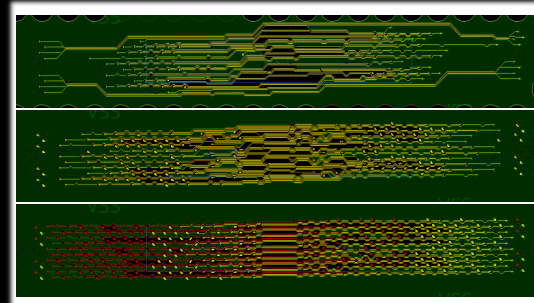
Chiplet Standardization

Alphawave collaboration underway for UCle layout and electrical simulation

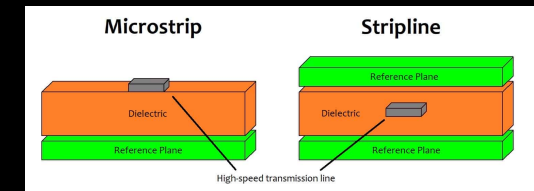
45 μ m Staggered Pitch
standard footprint



Gen 2 M-Series 5-RDL stack-up
three signal layers, two reference plane layers

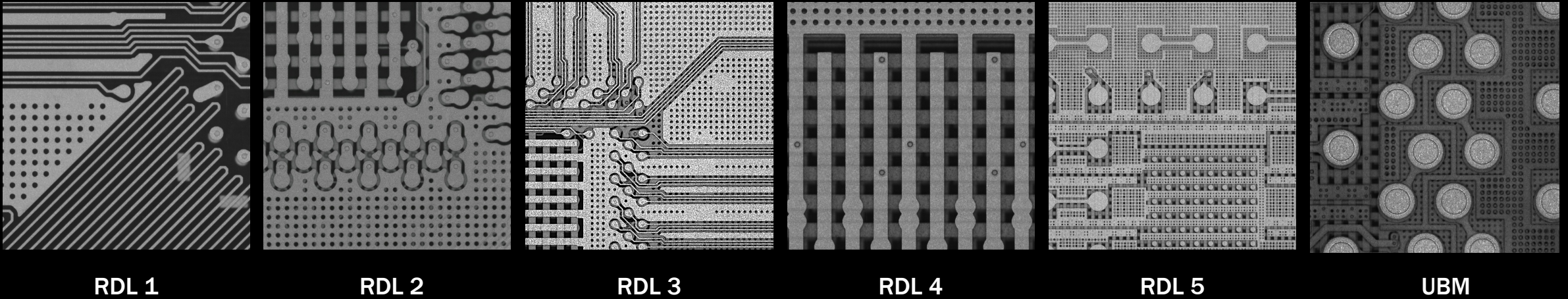


Optimized for low crosstalk
one stripline, two microstrip



Five Layer RDL on M-Series

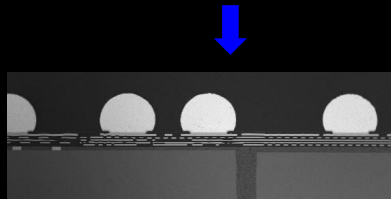
- Successfully designed & fabricated advanced CPU device - 24mm body size & 6 layers of metal (5 RDL + UBM)
- Second generation in 2023 delivers ultra-high-density chiplet integration with RDL-only solution



Phase 1
2022
Monolithic SoC



Phase 2
2023
Chiplet-based SoC

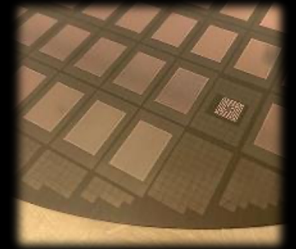


CPU device split into chiplets

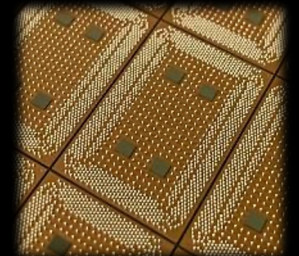
- 5-layer RDL (no bridge die req'd)
- 20 μm device bond pad pitch
- 60 μm die to die spacing
- Structural silicon added
- IPDs on UBM layer
- No bridge die required

Phase 1 device

- After panelization



- After IPD & ball attach

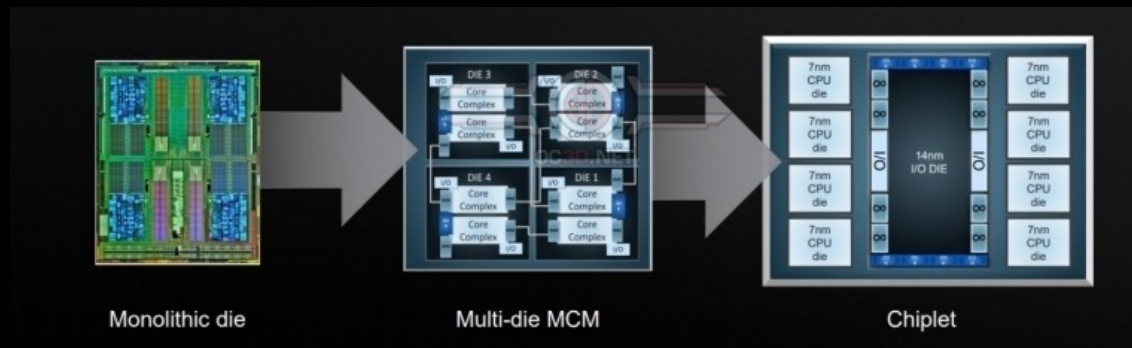


Outline

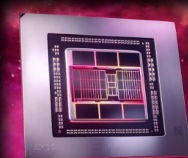
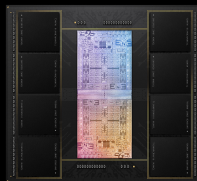
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Conclusion

Semiconductor industry is moving to chiplets & heterogeneous integration

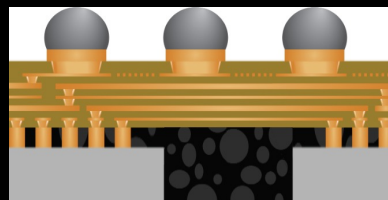


Advanced packaging technologies play a critical role today, and, in the future
Fan-out capabilities are already proving successful in chiplets today



AMD

New capabilities enable the next generation of fan-out density



Thank you from  **DECA**